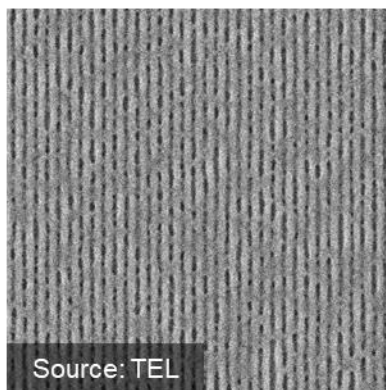
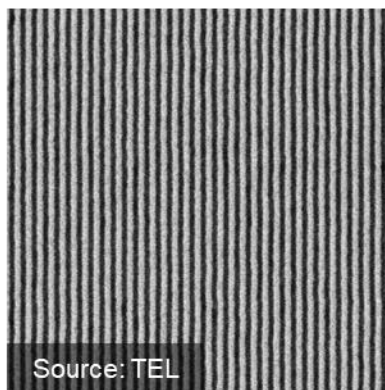


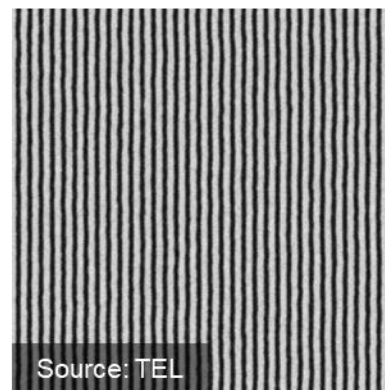
EUV-ADI, 36.75 mJ/cm²



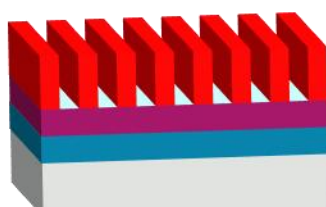
DSA-ADI



AEI, uLWR 3 σ = 1.6 nm



24 nm



Representative 819 nm × 819 nm CD-SEM images demonstrating rectification of a poor-quality prepattern generated by EUV lithography.